



Magna Park, Coventry Road, Lutterworth
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BD646; 648
 BD650; 652

SILICON DARLINGTON POWER TRANSISTORS

P-N-P epitaxial base transistors in monolithic Darlington circuit for audio output stages and general amplifier and switching applications; TO-220 plastic envelope. N-P-N complements are BD645, BD647, BD649 and BD651.

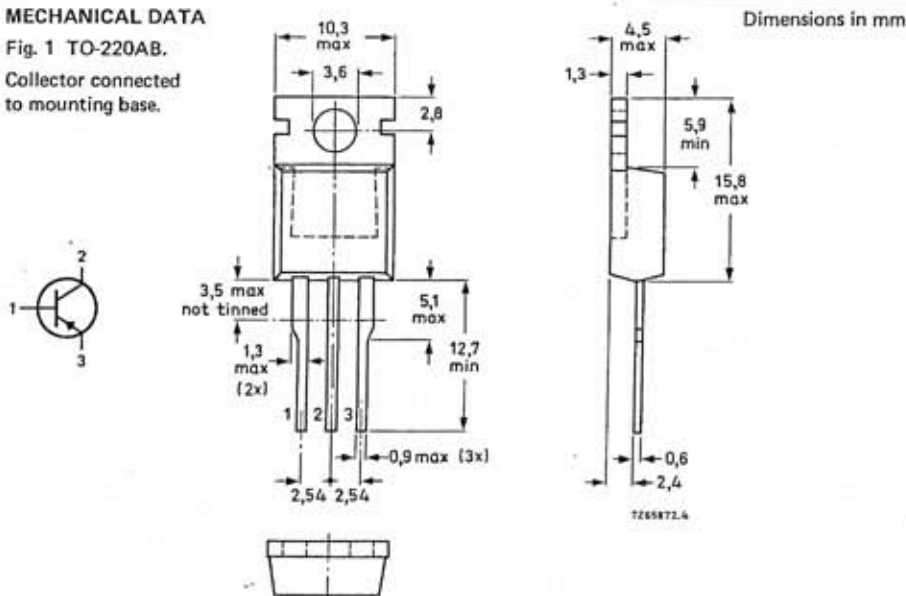
QUICK REFERENCE DATA

		BD646	648	650	652
Collector-base voltage (open emitter)	$-V_{CB0}$ max.	60	80	100	120 V
Collector-emitter voltage (open base)	$-V_{CEO}$ max.	60	80	100	120 V
Collector current (peak value)	$-I_{CM}$ max.		12		A
Total power dissipation up to $T_{mb} = 25^\circ\text{C}$	P_{tot} max.		62,5		W
Junction temperature	T_j max.		150		$^\circ\text{C}$
D.C. current gain:					
$-I_C = 0,5 \text{ A}; -V_{CE} = 3 \text{ V}$	h_{FE} typ.		2700		
$-I_C = 3,0 \text{ A}; -V_{CE} = 3 \text{ V}$	$h_{FE} >$		750		
Cut-off frequency:					
$-I_C = 3 \text{ A}; -V_{CE} = 3 \text{ V}$	f_{hfe} typ.		100		kHz

MECHANICAL DATA

Fig. 1 TO-220AB.

Collector connected to mounting base.



See also chapters Mounting Instructions and Accessories.

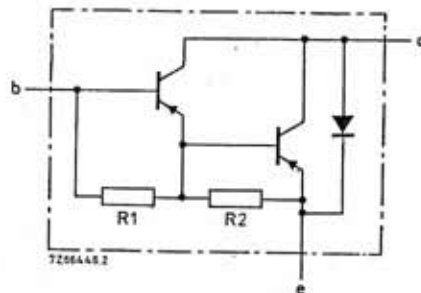


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R₁ typ. 4 kΩ
R₂ typ. 80 Ω

Fig. 2 Darlington circuit diagram.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

		BD646	648	650	652
Collector-base voltage (open emitter)	-V _{CB0} max.	60	80	100	120 V
Collector-emitter voltage (open base)	-V _{CEO} max.	60	80	100	120 V
Emitter-base voltage (open collector)	-V _{EBO} max.	5	5	5	5 V
Collector current (d.c.)	-I _C max.		8		A
Collector current (peak value)	-I _{CM} max.		12		A
Base current (d.c.)	-I _B max.		150		mA
Total power dissipation up to T _{mb} = 25 °C	P _{tot} max.		62,5		W
Storage temperature	T _{stg}	-65 to + 150			°C
Junction temperature *	T _j	150			°C

THERMAL RESISTANCE *

From junction to mounting base	R _{th j-mb} =	2	K/W
From junction to ambient in free air	R _{th j-a} =	70	K/W

* Based on maximum average junction temperature in line with common industrial practice. The resulting higher junction temperature of the output transistor part is taken into account.



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CHARACTERISTICS

 $T_j = 25^\circ\text{C}$ unless otherwise specified

Collector cut-off current

$$I_E = 0; -V_{CB} = -V_{CB0\text{max}} \quad -I_{CBO} < 0,2 \text{ mA}$$

$$I_E = 0; \begin{matrix} \text{BD646: } -V_{CB} = 40 \text{ V} \\ \text{BD648: } -V_{CB} = 50 \text{ V} \\ \text{BD650: } -V_{CB} = 60 \text{ V} \\ \text{BD652: } -V_{CB} = 70 \text{ V} \end{matrix}; T_j = 150^\circ\text{C} \quad -I_{CBO} < 2 \text{ mA}$$

$$I_B = 0; -V_{CE} = \frac{1}{2} V_{CE0\text{max}} \quad -I_{CEO} < 0,5 \text{ mA}$$

Emitter cut-off current

$$I_C = 0; -V_{EB} = 5 \text{ V} \quad -I_{EBO} < 5 \text{ mA}$$

D.C. current gain (note 1)

$$-I_C = 0,5 \text{ A}; -V_{CE} = 3 \text{ V} \quad h_{FE} \text{ typ. } 2700$$

$$-I_C = 3 \text{ A}; -V_{CE} = 3 \text{ V} \quad h_{FE} > 750$$

$$-I_C = 8 \text{ A}; -V_{CE} = 3 \text{ V} \quad h_{FE} \text{ typ. } 200$$

Base-emitter voltage (notes 1 and 2)

$$-I_C = 3 \text{ A}; -V_{CE} = 3 \text{ V} \quad -V_{BE} < 2,5 \text{ V}$$

Saturation voltages (note 1)

$$-I_C = 3 \text{ A}; -I_B = 12 \text{ mA} \quad -V_{CE\text{sat}} < 2 \text{ V}$$

$$-I_C = 5 \text{ A}; -I_B = 50 \text{ mA} \quad -V_{CE\text{sat}} < 2,5 \text{ V}$$

$$-V_{BE\text{sat}} < 3 \text{ V}$$

Collector capacitance at $f = 1 \text{ MHz}$

$$I_E = I_B = 0; -V_{CB} = 10 \text{ V} \quad C_c \text{ typ. } 75 \text{ pF}$$

Cut-off frequency

$$-I_C = 3 \text{ A}; -V_{CE} = 3 \text{ V} \quad f_{hfe} \text{ typ. } 100 \text{ kHz}$$

Small-signal current gain

$$-I_C = 3 \text{ A}; -V_{CE} = 3 \text{ V}; f = 1 \text{ MHz} \quad h_{fe} > 10 \quad \leftarrow$$

Diode, forward voltage

$$I_F = 3 \text{ A} \quad V_F \text{ typ. } 1,8 \text{ V}$$

Second-breakdown collector current

$$-V_{CE} = 50 \text{ V}; t_p = 0,1 \text{ s} \quad -I_{(SB)} > 1,25 \text{ A}$$

Switching times (between 10% and 90% levels) (Fig. 3)

$$-I_{Con} = 3 \text{ A}; -I_{Bon} = I_{Boff} = 12 \text{ mA}; V_{CC} = -10 \text{ V}$$

$$\text{Turn-on time} \quad t_{on} \text{ typ. } 1 \mu\text{s}$$

$$t_{on} < 2 \mu\text{s}$$

$$\text{Turn-off time} \quad t_{off} \text{ typ. } 5 \mu\text{s}$$

$$t_{off} < 10 \mu\text{s}$$

Notes

1. Measured under pulse conditions: $t_p < 300 \mu\text{s}$, $\delta < 2\%$.
2. $-V_{BE}$ decreases by about $3,8 \text{ mV/K}$ with increasing temperature.



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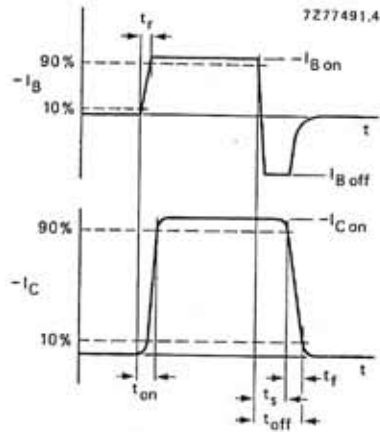


Fig. 3 Switching times waveforms.

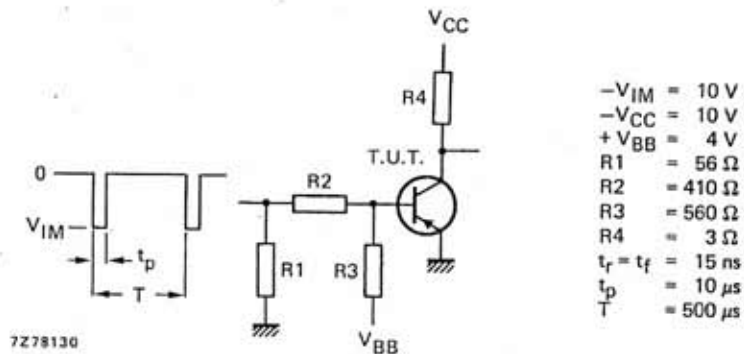


Fig. 4 Switching times test circuit.



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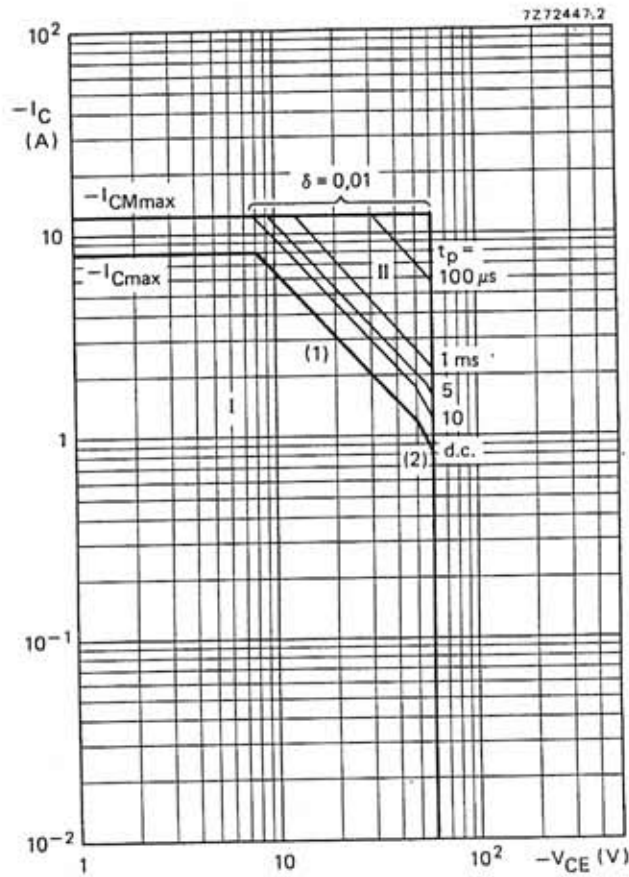


Fig. 5 Safe Operating Area transistor BD646 at $T_{mb} = 25\text{ }^{\circ}\text{C}$.

- I Region of permissible d.c. operation.
- II Permissible extension for repetitive pulse operation.
- (1) $P_{tot\ max}$ and $P_{peak\ max}$ lines.
- (2) Second-breakdown limits (independent of temperature).



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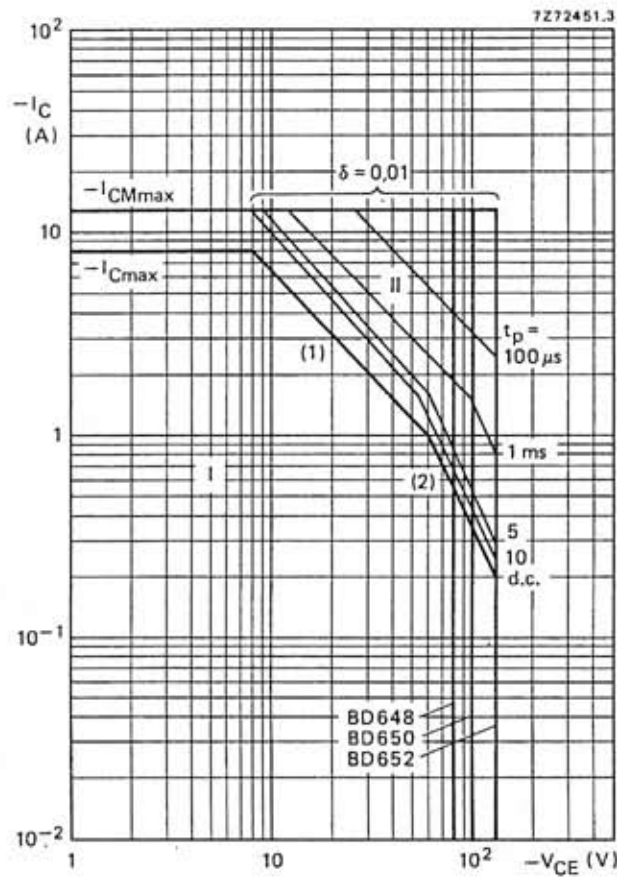


Fig. 6 Safe Operating Area. $T_{mb} = 25^\circ\text{C}$

- I Region of permissible d.c. operation.
- II Permissible extension for repetitive pulse operation.
- (1) $P_{tot\ max}$ and $P_{peak\ max}$ lines.
- (2) Second-breakdown limits (independent of temperature).



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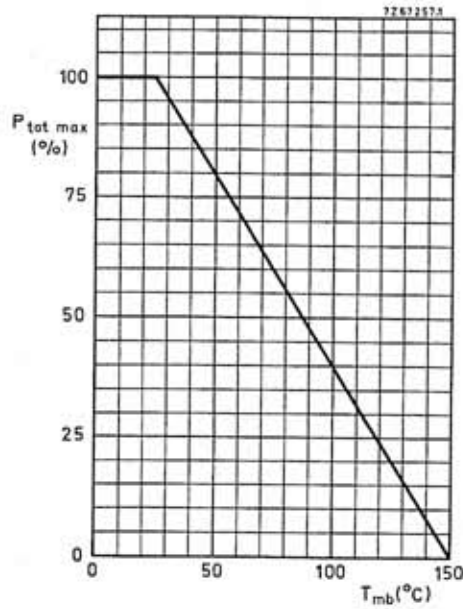


Fig. 7 Power derating curve.

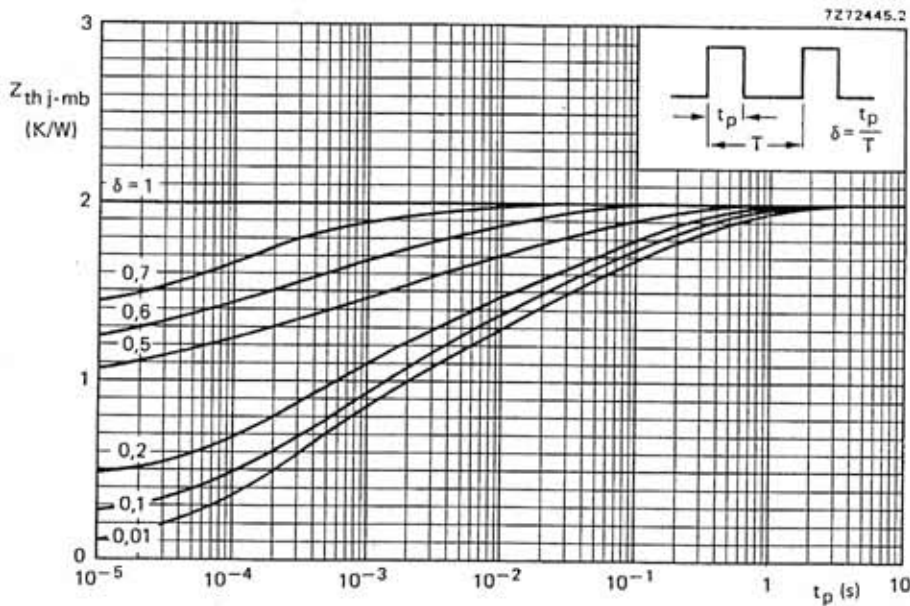


Fig. 8 Pulse power rating chart.



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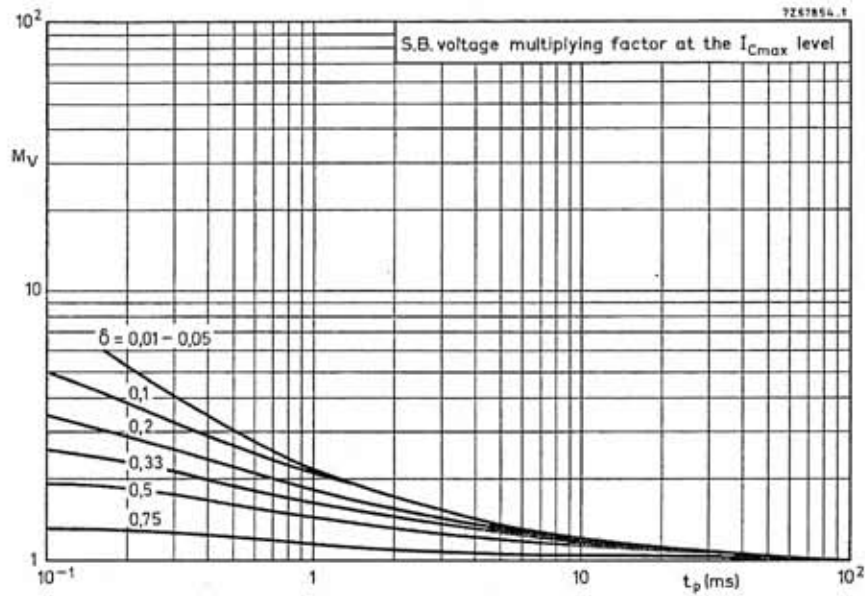


Fig. 9 S.B. voltage multiplying factor at the I_{Cmax} level.

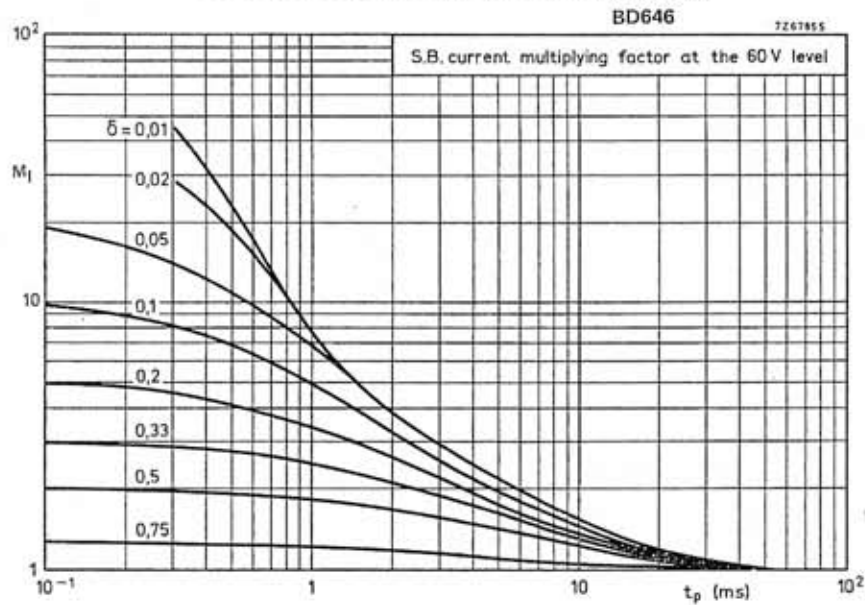


Fig. 10 S.B. current multiplying factor at 60 V level.



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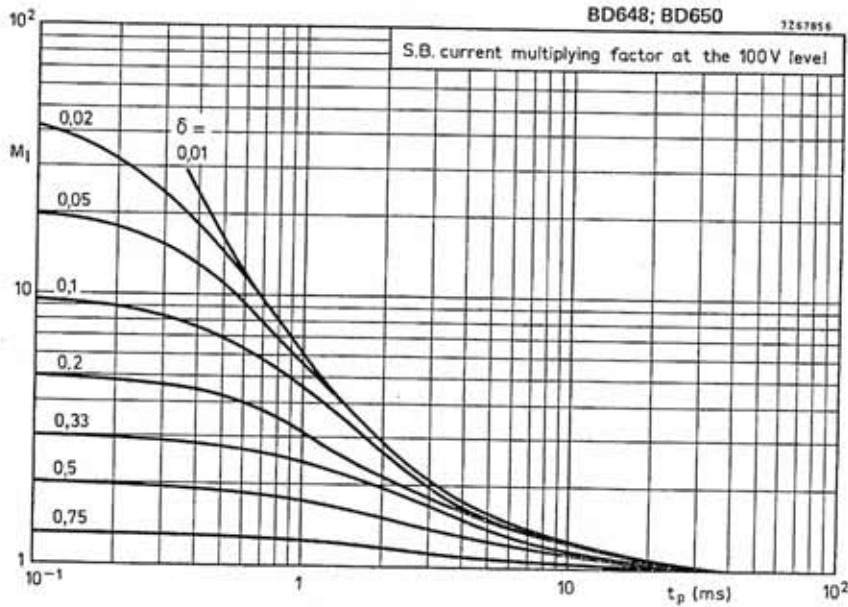


Fig. 11.

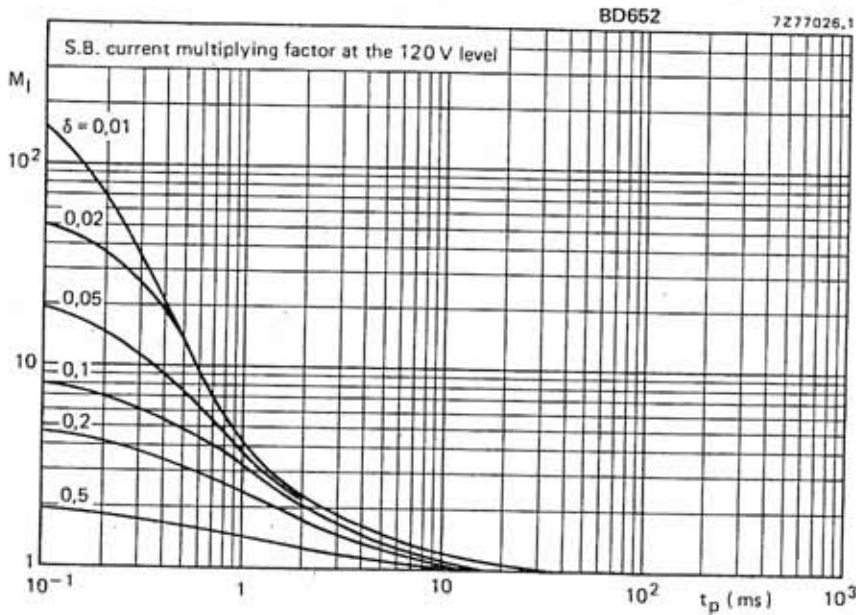


Fig. 12.



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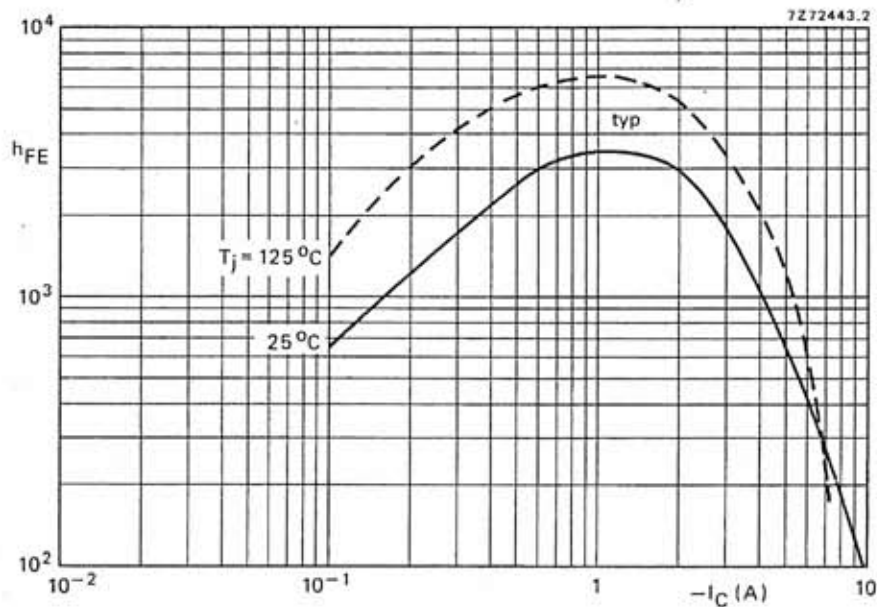


Fig. 13 D.C. current gain at $-V_{CE} = 3\text{ V}$.

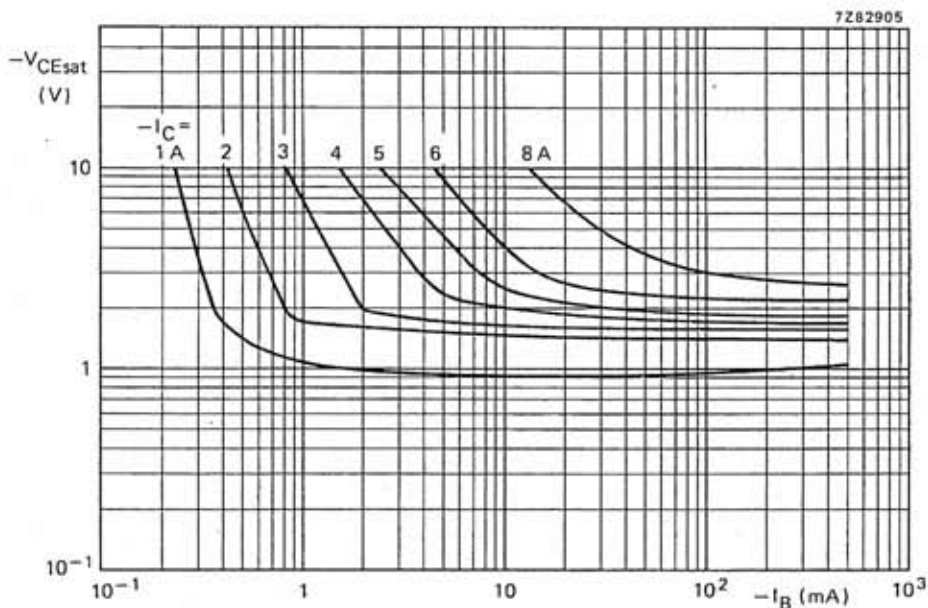


Fig. 14 Typical collector-emitter saturation voltage at $T_j = 25\text{ }^\circ\text{C}$.



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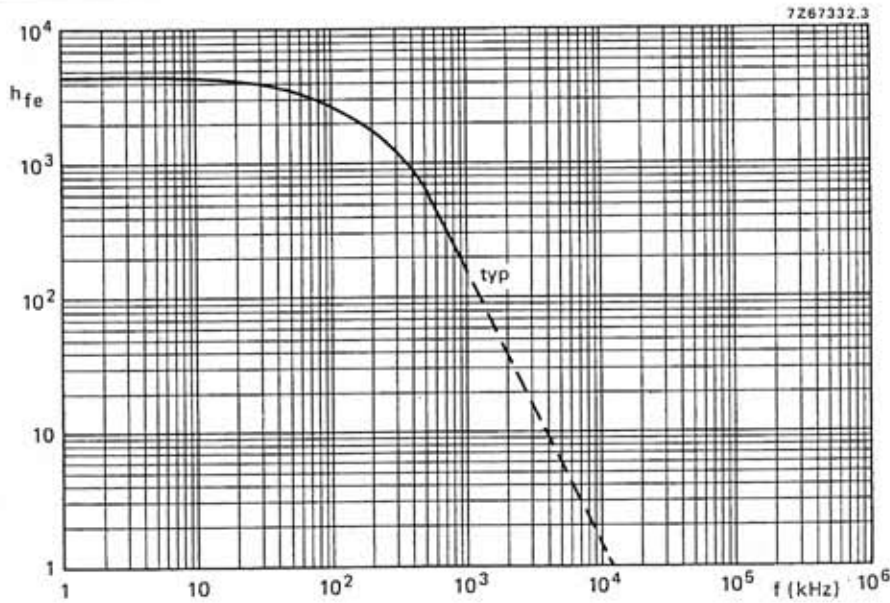


Fig. 15 Small signal current gain at $-I_C = 3\text{ A}$; $-V_{CE} = 3\text{ V}$.

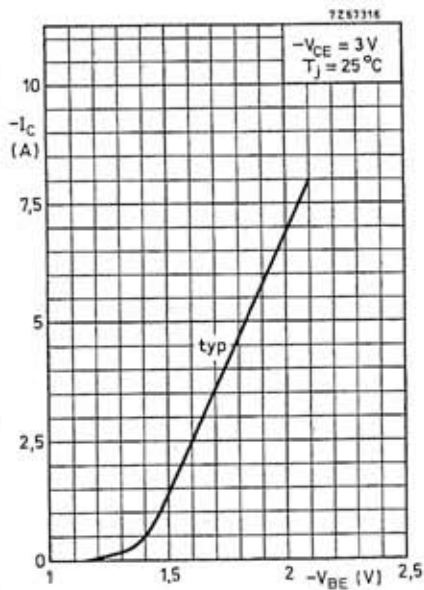


Fig. 16 Collector current.